FORM PTO-1449 (MODIFIED)

LIST OF PUBLICATIONS FOR

APPLICANT'S INFORMATION

DISCLOSURE STATEMENT

Applicant(s): Allen et al.

Docket No.: YOR920030175US1

Serial No.: 10/661,041

Filing Date: September 12, 2003

Group: 2811

	-	Ţ	J.S. PATENT DOCUMENTS		
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	filing date IP Appropriate
Cu	5,753,418	05/19/98	Tsai et al.	430/313	
an	6,009,888	01/04/00	Ye et al.	134/1.3	
on	6,316,167	11/13/01	Angelopoulos et al.	430/313	
Car	6,387,798	05/14/02	Loke et al.	438/623	
Can	6,514,867	02/04/03	Hui et al.	438/713	
		FOR	EIGN PATENT DOCUMENT	rs	
EXAMINER INITIAL	DOCUMENT NO.	DATOR	COUNTRY	CLASS/SUBCLASS	Translation YES NO
QL/	EP 0 236 220 A1	13/04/88	Europe	7	
			OTHER DOCUMENTS		
BXAMINER INITIAL	REP NO. AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.				
ar ar	Celii et al., "Process Characterization for Tapered Contact Etch," J. Vac. Sci. Technol. B 19(5), American Vacuum Society, Pgs. 1845-1851 (Sept/Oct 2001). Mahorowala et al., "Tunable Anti-Reflective Coatings with Built-In Hard Mask Properties Facilitating Thin Resist Processing," Proceedings of the SPIE, Vol. 4343, Pgs. 306-316 (2001).				

Examiner Examiner

Date Considered

61-06-05

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

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ou/	6,387,798	05/14/02	Loke et al.	438/623	
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	American Vacuur	n Society, Pg	ization for Tapered Contact Etch," J. s. 1845-1851 (Sept/Oot 2001).		• • •
	Mahorowala et al., "Tunable Anti-Reflective Coatings with Built-In Hard Mask Properties Facilitating Thin Resist Processing," Proceedings of the SPIE, Vol. 4343, Pgs. 306-316 (2001).				

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<u>u</u> _	Chun et al., "Contact Hole Size Reducing Methods by Using Water-Soluble Organic Over-Coating Material (WASOOM) as a Barrier Layer Toward 0.15 um Contact Hole; Resist Flow Technique I," Proc. SPIE, Vol. 3999, pgs. 620-626 (2000).				
4	Chung et al., "A Novel Resist Material for sub-100 nm Contact Hole Pattern," Proc. SPIE, Vol. 3999, pgs. 305-312 (2000).				
G	DellaGuardia et al., "193 Lithography and RELACS™ Processing for BBOL Lithography," Proc. SPIE, Vol. 4346, pgs. 1029-1040 (2001).				
	Lucas et al., "193 nm Contact Photoresist Reflow Feasibility Study," Proc. SPIE, Vol. 4345, pgs. 725-736 (2001).				
	Satou et al., "Su Lithography," J	ib-0.10 µm Hol pn. J. Appl. Phy	e Fabrication Using Bilayer Sily ys. 1, Vol. 38, Part 1, No. 12B, p	rlation Process for 193 pegs 7008-7012 (Decemb	am er 1999).

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